

APPLICATION DATA SHEET

Application Information

Application Type:: Regular
Subject Matter:: Utility
Title:: SILICON ON INSULATOR STRUCTURE
FROM LOW DEFECT DENSITY SINGLE
CRYSTAL SILICON
Attorney Docket Number:: MEMC 98-3052(2512.2)
Request for Early Publication?:: No
Request for Non-Publication?:: No
Total Drawing Sheets:: 35
Small Entity?:: No
Petition Included?:: No
Secrecy Order in Parent?:: No

Applicant Information

Applicant Authority Type:: Inventor
Primary Citizenship Country:: US
Status:: Full Capacity
Given Name:: Robert
Middle Name:: J.
Family Name:: Falster
City of Residence:: London
Country of Residence:: England
Street of Mailing Address:: 508 Pearl Drive, P.O. Box 8
City of Mailing Address:: St. Peters
State or Province of Mailing
Address:: MO
Postal Code of Mailing Address:: 63376

Correspondence Information

Correspondence Customer Number:: 000321

Representative Information

Representative Customer Number:: 000321

Domestic Priority Information

Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This application	Division of	09/737,715	12/15/00
09/737,715	Continuation of	09/387,288	08/31/99
09/387,288	Non- Provisional of	60/098,902	09/02/98

Assignee Information

Assignee Name:: MEMC Electronic Materials, Inc.